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AUTHOR’S RELEVANT PUBLICATIONS

Journals:

1. **Ashish Kumar Singh,** Manas Ranjan. Tripathy, Kamalaksha Baral, Prince Kumar Singh, and Satyabrata Jit, “Impact of interface trap charges on device level performances of a lateral / vertical gate stacked Ge / Si TFET on SELBOX substrate,” *Appl. Phys. A*, vol. 126, no. 9, pp. 1–11, 2020, doi: 10.1007/s00339-020-03869-9.
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